

L Number	Hits	Search Text	DB	Time stamp
1	923	361/305	USPAT; US-PGPUB	2003/12/23 14:50
4	69	361/305 and (tantalum adj nitride "tan.sub.x")	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/12/23 14:51
5	7	361/305 and (tantalum adj nitride "tan.sub.x") and (work adj function workfunction)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/12/23 14:59
6	1	257/304.cccls. and (tantalum adj nitride "tan.sub.x") and (work adj function workfunction)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/12/23 15:00
7	10	257/310.cccls. and (tantalum adj nitride "tan.sub.x") and (work adj function workfunction)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/12/23 15:03
8	956	361/305	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/12/23 15:03
9	0	361/305 and (tantalum adj nitride "tan.sub."\$1) near15 (work adj function workfunction)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/12/23 15:08
10	228	361/305 and semiconductor.ti,ab,clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/12/23 15:08
11	588	(361/303).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/12/23 15:08
12	0	((361/303).CCLS.) and (tantalum adj nitride "tan.sub."\$1) near15 (work adj function workfunction)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/12/23 15:20
13	133	(257/906).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/12/23 15:21
14	1	((257/906).CCLS.) and (tantalum adj nitride "tan.sub."\$2)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/12/23 15:22
15	553	(257/288).CCLS.	USPAT; US-PGPUB	2003/12/23 15:22
16	16	((257/288).CCLS.) and (tantalum adj nitride "tan.sub."\$2)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/12/23 15:35
17	6732	((257/68) or (257/71) or (257/213) or (257/288) or (257/296) or (257/300) or (257/304) or (257/306) or (257/308) or (257/309) or (257/310) or (257/311) or (257/761) or (257/763) or (257/906) or (361/303) or (361/305) or (361/306.1) or (361/306.3)).CCLS.	USPAT; US-PGPUB	2003/12/23 15:37

18	4	((257/68) or (257/71) or (257/213) or (257/288) or (257/296) or (257/300) or (257/304) or (257/306) or (257/308) or (257/309) or (257/310) or (257/311) or (257/761) or (257/763) or (257/906) or (361/303) or (361/305) or (361/306.1) or (361/306.3)).CCLS.) and (workfunction work adj function) near12 (tantalum adj nitride "tan.sub.S2")	USPAT; US-PGPUB	2003/12/23 15:38
-	6085	((257/68) or (257/71) or (257/296) or (257/300) or (257/306) or (257/308) or (257/309) or (257/310) or (257/311) or (257/761) or (257/763) or (361/303) or (361/305) or (361/306.1) or (361/306.3) or (361/311)).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/15 10:38
-	23	((("257/68") or ("257/71") or ("257/296")) or ("257/300") or ("257/306") or ("257/308") or ("257/309") or ("257/310") or ("257/311") or ("257/761") or ("257/763") or ("361/303") or ("361/305") or ("361/306.1") or ("361/306.3") or ("361/311")).CCLS.) and semiconductor and capacitor and (tantalum adj oxide or tantalum adj pentoxide) and tantalum adj nitride and tungsten and substrate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/08/23 08:46
-	0	6285072.pn.	JPO; DERWENT	2001/08/22 18:20
-	3	((("257/68") or ("257/71") or ("257/296")) or ("257/300") or ("257/306") or ("257/308") or ("257/309") or ("257/310") or ("257/311") or ("257/761") or ("257/763") or ("361/303") or ("361/305") or ("361/306.1") or ("361/306.3") or ("361/311")).CCLS.) and semiconductor and capacitor and (tantalum adj oxide or tantalum adj pentoxide) and indium adj oxide and tungsten and substrate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/08/22 20:49
-	2	((("257/68") or ("257/71") or ("257/296")) or ("257/300") or ("257/306") or ("257/308") or ("257/309") or ("257/310") or ("257/311") or ("257/761") or ("257/763") or ("361/303") or ("361/305") or ("361/306.1") or ("361/306.3") or ("361/311")).CCLS.) and semiconductor and capacitor and (tantalum adj oxide or tantalum adj pentoxide) and indium adj oxide and tungsten and substrate and tantalum adj nitride	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/08/23 08:49
-	0	semiconductor and capacitor and (tantalum adj oxide or tantalum adj pentoxide) and tantalum adj nitride and tungsten and substrate	EPO; JPO; IBM_TDB	2001/08/23 08:47
-	8	semiconductor and capacitor and (tantalum adj oxide or tantalum adj pentoxide) and indium adj oxide and tungsten and substrate and tantalum adj nitride	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/08/23 08:48
-	0	semiconductor and capacitor and (tantalum adj oxide or tantalum adj pentoxide) and indium adj oxide and tungsten and substrate and tantalum adj nitride	EPO; JPO; DERWENT; IBM_TDB	2001/08/23 08:48
-	2	((("257/68") or ("257/71") or ("257/296")) or ("257/300") or ("257/306") or ("257/308") or ("257/309") or ("257/310") or ("257/311") or ("257/761") or ("257/763") or ("361/303") or ("361/305") or ("361/306.1") or ("361/306.3") or ("361/311")).CCLS.) and semiconductor and capacitor and (tantalum adj oxide or tantalum adj pentoxide) and indium adj oxide and substrate and tantalum adj nitride	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/08/23 08:50

	0	semiconductor and capacitor and (tantalum adj oxide or tantalum adj pentoxide) and indium adj oxide and substrate and tantalum adj nitride	EPO; JPO; IBM_TDB	2001/08/23 08:50
	0	semiconductor and (capacitor or dram) and (tantalum adj oxide or tantalum adj pentoxide) and indium adj oxide and tantalum adj nitride	EPO; JPO; IBM_TDB	2001/08/23 08:51
	0	(tantalum adj nitride with work adj function) and semiconductor and dram and capacitor	USPAT; US_PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/08/23 10:38
	1	(tantalum adj nitride with work adj function) and semiconductor and capacitor	USPAT; US_PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/08/23 10:40
	12	(tantalum adj nitride with work adj function) and (257/\$5.cccls. or 438/\$5.cccls.)	USPAT; US_PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/08/23 10:41
	3	4663559.pn.	USPAT; US_PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/08/23 11:16
	0	barrier with tantal\$2 adj nitride with ev	USPAT; US_PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/08/23 11:47
	522	barrier with tantal\$2 adj nitride	USPAT; US_PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/08/23 11:47
	0	diffusion adj barrier with tantal\$2 adj nitride with work adj function	USPAT; US_PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/08/23 11:48
	0	diffusion adj barrier with tantal\$2 adj nitride same work adj function	USPAT; US_PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/08/23 11:48
	0	(diffusion adj barrier with tantal\$2 adj nitride) same work adj function	USPAT; US_PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/08/23 11:48
	0	(diffusion adj barrier with tant\$4 adj nitride) same work adj function	USPAT; US_PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/08/23 11:49
	1	(diffusion adj barrier with tant\$4 adj nitride) and (tant\$4 adj nitride same work adj function)	USPAT; US_PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/08/23 12:06
	0	diffusion adj barrier with tant\$4 adj nitride with indium adj oxide	USPAT; US_PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/08/23 12:06

	3	(diffusion adj barrier with tant\$4 adj nitride) and (semiconductor.ti,ab. and capacitor.ti,ab.)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/08/23 12:38
	1	(leakage adj current with tant\$4 adj nitride) and (semiconductor.ti,ab. and capacitor.ti,ab.)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/08/23 12:42
	17	(barrier with tant\$4 adj nitride) and (semiconductor.ti,ab. and capacitor.ti,ab.)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/08/23 12:52
	2	jp-10320569\$--.did.	JPO; DERWENT	2001/08/23 19:32
	626	effective adj refractive adj index	JPO; DERWENT	2001/08/23 19:33
	99	effective adj refractive adj index near10 mode	JPO; DERWENT	2001/08/23 19:33
	61	effective adj refractive adj index near4 mode	JPO; DERWENT	2001/08/23 19:34
	310	effective adj refractive adj index near4 mode	USPAT; US-PGPUB; EPO; DERWENT; IBM_TDB	2001/08/23 19:34
	26	effective adj refractive adj index with waveguide adj mode	USPAT; US-PGPUB; EPO; DERWENT; IBM_TDB	2001/08/23 19:34
	6349	((257/68) or (257/71) or (257/296) or (257/300) or (257/306) or (257/308) or (257/309) or (257/310) or (257/311) or (257/761) or (257/763) or (361/303) or (361/305) or (361/306.1) or (361/306.3) or (361/311)).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/12/10 13:36
	0	("L4 and (indium adj2 oxide near10 (storage or first or second or cell) adj2 electrode)").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/12/10 13:39
	1	((("257/68") or ("257/71") or ("257/296") or ("257/300") or ("257/306") or ("257/308") or ("257/309") or ("257/310") or ("257/311") or ("257/761") or ("257/763") or ("361/303") or ("361/305") or ("361/306.1") or ("361/306.3") or ("361/311")).CCLS.) and (indium adj2 oxide near10 (storage or first or second or cell) adj2 electrode)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/12/10 13:43
	6	((("257/68") or ("257/71") or ("257/296") or ("257/300") or ("257/306") or ("257/308") or ("257/309") or ("257/310") or ("257/311") or ("257/761") or ("257/763") or ("361/303") or ("361/305") or ("361/306.1") or ("361/306.3") or ("361/311")).CCLS.) and (indium adj2 oxide same (storage or first or second or cell) adj2 electrode)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/12/10 14:03
	9	((("257/68") or ("257/71") or ("257/296") or ("257/300") or ("257/306") or ("257/308") or ("257/309") or ("257/310") or ("257/311") or ("257/761") or ("257/763") or ("361/303") or ("361/305") or ("361/306.1") or ("361/306.3") or ("361/311")).CCLS.) and (indium adj oxide same electrode) and capacitor.ti,ab.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/12/10 14:51

	1	((("257/68") or ("257/71") or ("257/296") or ("257/300") or ("257/306") or ("257/308") or ("257/309") or ("257/310") or ("257/311") or ("257/761") or ("257/763") or ("361/303") or ("361/305") or ("361/306.1") or ("361/306.3") or ("361/311")).CCLS.) and (purpose same indium adj oxide same electrode) and capacitor.ti,ab.	USPAT; US~PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/12/10 15:17
	2	((("257/68") or ("257/71") or ("257/296") or ("257/300") or ("257/306") or ("257/308") or ("257/309") or ("257/310") or ("257/311") or ("257/761") or ("257/763") or ("361/303") or ("361/305") or ("361/306.1") or ("361/306.3") or ("361/311")).CCLS.) and (purpose same indium adj oxide same electrode)	USPAT; US~PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/12/10 15:06
	0	((("257/68") or ("257/71") or ("257/296") or ("257/300") or ("257/306") or ("257/308") or ("257/309") or ("257/310") or ("257/311") or ("257/761") or ("257/763") or ("361/303") or ("361/305") or ("361/306.1") or ("361/306.3") or ("361/311")).CCLS.) and ((tungsten or w) near4 (plug or via)) and (electrode same indium adj oxide) and (dielectric near10 (tantalum adj oxide or tantalum adj pentoxide)) and (capacitor or dram).ti,ab.	USPAT; US~PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/12/10 15:10
	0	((("257/68") or ("257/71") or ("257/296") or ("257/300") or ("257/306") or ("257/308") or ("257/309") or ("257/310") or ("257/311") or ("257/761") or ("257/763") or ("361/303") or ("361/305") or ("361/306.1") or ("361/306.3") or ("361/311")).CCLS.) and ((tungsten or w) near4 (plug or via)) and (electrode same indium adj oxide) and ((insulating or insulator or dielectric) near10 (tantalum adj oxide or tantalum adj pentoxide)) and (capacitor or dram or electrode).ti,ab.	USPAT; US~PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/12/10 15:13
	0	((("257/68") or ("257/71") or ("257/296") or ("257/300") or ("257/306") or ("257/308") or ("257/309") or ("257/310") or ("257/311") or ("257/761") or ("257/763") or ("361/303") or ("361/305") or ("361/306.1") or ("361/306.3") or ("361/311")).CCLS.) and ((tungsten or w) near4 (plug or via)) and (electrode same indium adj oxide) and ((insulating or insulator or dielectric) near10 (tantalum adj oxide or tantalum adj pentoxide))	USPAT; US~PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/12/10 15:14
	0	((("257/68") or ("257/71") or ("257/296") or ("257/300") or ("257/306") or ("257/308") or ("257/309") or ("257/310") or ("257/311") or ("257/761") or ("257/763") or ("361/303") or ("361/305") or ("361/306.1") or ("361/306.3") or ("361/311")).CCLS.) and ((tungsten or w) near12 (plug or via)) and (electrcde same indium adj oxide) and ((insulating or insulator or dielectric) near12 (tantalum adj oxide or tantalum adj pentoxide))	USPAT; US~PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/12/10 15:15
	1	((("257/68") or ("257/71") or ("257/296") or ("257/300") or ("257/306") or ("257/308") or ("257/309") or ("257/310") or ("257/311") or ("257/761") or ("257/763") or ("361/303") or ("361/305") or ("361/306.1") or ("361/306.3") or ("361/311")).CCLS.) and (electrode same indium adj oxide) and ((insulating or insulator or dielectric) near12 (tantalum adj oxide or tantalum adj pentoxide))	USPAT; US~PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/12/10 15:36

	0	((("257/68") or ("257/71") or ("257/296") or ("257/300") or ("257/306") or ("257/308") or ("257/309") or ("257/310") or ("257/311") or ("257/761") or ("257/763") or ("361/303") or ("361/305") or ("361/306.1") or ("361/306.3") or ("361/311")).CCLS.) and (electrode same indium adj oxide) and ((insulating or insulator or dielectric) near12 (tantalum adj oxide or tantalum adj pentoxide)) and (dram or capacitor).ti,ab.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/12/10 15:17
	0	((("257/68") or ("257/71") or ("257/296") or ("257/300") or ("257/306") or ("257/308") or ("257/309") or ("257/310") or ("257/311") or ("257/761") or ("257/763") or ("361/303") or ("361/305") or ("361/306.1") or ("361/306.3") or ("361/311")).CCLS.) and (electrode same indium adj oxide) and ((insulating or insulator or dielectric) near12 (tantalum adj oxide or tantalum adj pentoxide)) and (dram or capacitor)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/12/10 15:17
	0	((("257/68") or ("257/71") or ("257/296") or ("257/300") or ("257/306") or ("257/308") or ("257/309") or ("257/310") or ("257/311") or ("257/761") or ("257/763") or ("361/303") or ("361/305") or ("361/306.1") or ("361/306.3") or ("361/311")).CCLS.) and ((reductive or protection or protecting or protect) same tantalum adj nitride same indium adj oxide)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/12/10 15:37
	0	(tantalum adj nitride near12 indium adj oxide) same (protect or protection or protecting or protection)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/12/10 15:39
	0	(tantalum adj nitride same indium adj oxide) same (protect or protection or protecting or protection)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/12/10 15:40
	33	tantalum adj nitride same indium adj oxide	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/12/10 15:40
	0	tantalum adj nitride same indium adj oxide same (protect or cover or reduct\$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/12/10 15:41
	1815	((("257/68") or ("257/71") or ("257/296") or ("257/300") or ("257/306") or ("257/308") or ("257/309") or ("257/310") or ("257/311") or ("257/761") or ("257/763") or ("361/303") or ("361/305") or ("361/306.1") or ("361/306.3") or ("361/311")).CCLS.) and capacitor.ti,ab. and (electrode near4 indium oxide)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/12/10 15:44
	1815	((("257/68") or ("257/71") or ("257/296") or ("257/300") or ("257/306") or ("257/308") or ("257/309") or ("257/310") or ("257/311") or ("257/761") or ("257/763") or ("361/303") or ("361/305") or ("361/306.1") or ("361/306.3") or ("361/311")).CCLS.) and capacitor.ti,ab. and (electrode near2 indium oxide)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/12/10 15:44

	1	((("257/68") or ("257/71") or ("257/296") or ("257/300") or ("257/306") or ("257/308") or ("257/309") or ("257/310") or ("257/311") or ("257/761") or ("257/763") or ("361/303") or ("361/305") or ("361/306.1") or ("361/306.3") or ("361/311"))).CCLS.) and capacitor.ti,ab. and (electrode near2 indium adj oxide)	USPAT; US~PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/12/10 15:44
	2	hop near3 silicon adj substrate	USPAT; US~PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/12 10:16
	2	("6168991").PN.	USPAT; US~PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/12 13:01
	2	("6211005").PN.	USPAT; US~PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/12 14:08
	0	("adhesion near3 tungsten near3 (indium oxide or ito)").PN.	USPAT; US~PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/12 14:08
	41	adhesion near3 tungsten near3 (indium oxide or ito)	USPAT; US~PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/12 14:09
	0	adhesion near3 tungsten near3 (indium adj oxide or ito)	USPAT; US~PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/12 14:10
	0	adhesion near6 tungsten near6 (indium adj oxide or ito)	USPAT; US~PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/12 14:10
	0	adhesi\$2 near6 tungsten near6 (indium adj oxide or ito)	USPAT; US~PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/12 14:16
	0	tungsten near3 (plug or contact) near6 (indium adj oxide or ito) and dram.ti,ab.	USPAT; US~PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/12 14:17
	2	tungsten near3 (indium adj oxide or ito) and dram.ti,ab.	USPAT; US~PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/12 15:44
	2	tungsten near6 (indium adj oxide or ito) and dram.ti,ab.	USPAT; US~PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/12 15:45
	2	tungsten near12 (indium adj oxide or ito) and dram.ti,ab.	USPAT; US~PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/12 15:45

	494	tungsten near12 (indium adj oxide or ito)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/07/12 15:46
	1	tungsten near12 (indium adj oxide or ito) near12 (adhere or adhesion)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/07/12 15:47
	1	tungsten near12 (indium adj oxide or ito) near12 (adhere or adhesion or adhesive)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/07/12 16:03
	1	(w or tungsten) near12 (indium adj oxide or ito) near12 (adhere or adhesion or adhesive)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/07/12 16:23
	21	(w or tungsten) near12 (prevent or preventing) near12 oxidation near12 (contact or plug)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/07/12 16:36
	1	(prevent or preventing) near12 oxidation near12 indium adj oxide	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/07/12 16:49
	7	(tantalum adj nitride or tan) near12 (tungsten or w) near12 (indium adj oxide or ito or indium adj tin adj oxide)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/07/12 16:53
	530	(tantalum adj nitride or tan) near12 (tungsten or w) near12 (barrier or passivation)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/07/12 16:53
	53	(tantalum adj nitride or tan) near3 (tungsten or w) near3 (barrier or passivation)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/07/12 16:54
	5	(tantalum adj nitride or tan) near3 (tungsten or w) near3 (barrier or passivation).ti,ab.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/07/12 16:58
	135	(tantalum adj nitride or tan) near3 (tungsten or w).ti,ab.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/07/12 17:18
	8	(tantalum adj nitride or tan) near3 (tungsten or w).ti.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/07/12 17:26
	277	(tantalum adj nitride or tan) near3 (tungsten or w) near12 barrier	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/07/12 17:27
	18	(tantalum adj nitride or tan) near3 (tungsten or w) near12 barrier.ti,ab.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/07/12 19:16

-	0	(tantalum adj nitride or tan) (indium adj2 oxide or ito) near12 barrier.ti,ab.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT;	2002/07/12 18:08
-	2	("6265260").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT;	2002/07/12 19:17
-	2	("6168991").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT;	2002/07/12 19:39
-	0	("oxidation adj potential near12 (tungsten or W)").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT;	2002/07/12 19:39
-	55	oxidation adj potential near12 (tungsten or W)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT;	2002/07/12 19:40
-	21	"5166089"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT;	2002/07/15 14:16
-	3	("5166089").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT;	2002/07/15 14:17
-	3	("5235201").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT;	2002/07/15 14:17
-	17	(JS-5274482-\$ or US-4663559-\$ or US-5644151-\$ or US-6028360-\$ or US-5811851-\$ or US-5554866-\$ or US-6004839-\$ or US-5691220-\$ or US-5826129-\$ or US-5965942-\$ or US-6265260-\$ or US-6255151-\$ or US-6271596-\$ or US-6204076-\$).did. or (JP-10320569-\$ or JP-09246494-\$).did. or (EP-539197-\$).did.	USPAT; JPO; DERWENT	2002/12/09 10:17
-	0	tantalum adj nitride near20 work adj function.ti,ab.	USPAT; JPO; DERWENT	2002/12/09 10:18
-	1	tantalum adj nitride same work adj function.ti,ab.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT;	2002/12/09 10:18
-	3	bcc-tantalum	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT;	2002/12/09 14:08
-	0	".beta.-tantalum"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT;	2002/12/09 14:04
-	0	".beta. -tantalum"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/12/09 14:04

-	0	".alpha.-tantalum"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT;	2002/12/09 14:04 2002/12/09 14:05 2002/12/09 14:05 2002/12/09 14:06 2002/12/09 14:14 2002/12/09 14:14
-	0	".beta." adj tantalum	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT;	2002/12/09 14:05
-	0	".beta."-tantalum	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT;	2002/12/09 14:05
-	0	".beta.-tantalum"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT;	2002/12/09 14:06
-	9	bcc adj tantalum	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT;	2002/12/09 14:14
-	148	work adj function with tantalum	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT;	2002/12/09 14:14
-	0	work adj function with tetragonal adj tantalum	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT;	2002/12/09 14:14
-	119	work adj function near12 tantalum	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT;	2002/12/09 16:28
-	2	("6130123").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT;	2002/12/09 14:18
-	2	("6211005").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT;	2002/12/09 17:42
-	25	perovskite near12 tantalum adj oxide	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT;	2002/12/09 17:43
-	4	tantalum adj pentoxide near12 crystal adj structure	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT;	2002/12/10 14:24
-	2287	((("257/68") or ("257/71") or ("257/296") or ("257/300") or ("257/306") or ("257/308") or ("257/309") or ("257/310") or ("257/311") or ("257/761") or ("257/763") or ("361/303") or ("361/305") or ("361/306.1") or ("361/306.3") or ("361/311"))).CCLS.) and capacitor.ti,ab. and (electrode near12 indium oxide)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/10 14:49

	4	499037.ap.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/14 13:25
	2	barnak.in. and chau.in. and liang.in.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/14 13:30
	0	(contact or plug) near6 (tungsten w) and storage adj electrode near6 ("tan.sub.x" tantalum adj nitride) and (dielectric insulat\$3 capacit\$4) near6 ("ta.sub.2 o.sub.5" tantalum adj oxide) and (cell adj plate adj electrode or electrode) near6 ("ta.sub.2 c.sub.5" tantalum adj oxide)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/14 13:36
	0	(contact or plug) near6 (tungsten w) and storage adj electrode near6 ("tan.sub.x" tantalum adj nitride) and (dielectric insulat\$3 capacit\$4) near6 ("ta.sub.2 o.sub.5" tantalum adj oxide) and (cell adj plate adj electrode or electrode) near6 ("tan.sub.x" tantalum adj nitride)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/14 13:37
	7	(contact or plug) near6 (tungsten w) and (dielectric insulat\$3 capacit\$4) near6 ("ta.sub.2 o.sub.5" tantalum adj oxide) and (cell adj plate adj electrode or electrode) near6 ("tan.sub.x" tantalum adj nitride)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/14 14:26
	0	crystal adj growth near12 non-parallel near12 channel	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/14 14:29
	27	crystal adj growth near12 parallel near12 channel	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/14 14:33
	0	crystal adj growth near12 nonparallel near12 channel	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/14 14:33
	1	crystal adj growth near12 acute near12 channel	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/14 14:34
	7	work adj function near12 ("tan.sub.x" tantalum adj nitride) near12 ev	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/14 16:25
	25	(tantalum adj oxide tantalum adj pentoxide "ta.sub.2 o.sub.5") near6 dielectric near6 prefer\$4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/14 20:40
	4	((tantalum adj oxide tantalum adj pentoxide "ta.sub.2 o.sub.5") near6 dielectric near6 prefer\$4) and strontium	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/14 16:29
	20	strontium adj bismuth adj tantalum adj oxide and dielectric adj constant	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/14 16:29

	0	strontium adj bismuth adj tantalum adj oxide near20 dielectric adj constant	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/14 16:37
	0	"sr bi.sub.2 ta.sub.2 o.sub9" near12 (permittivity dielectric adj constant)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/14 16:38
	0	"sr bi.sub.2 ta.sub.2 o.sub9"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/14 16:38
	0	"srbi.sub.2 ta.sub.2 o.sub9"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/14 16:39
	2	("6211005").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/14 16:44
	0	(""indium oxide ("").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/14 16:44
	24	"indium oxide ("	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/14 16:45
	0	indium adj oxide and "in o.sub"\$2	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/14 16:46
	12777	indium adj oxide	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/14 16:46
	1410	indium adj oxide.ti.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/14 16:46
	0	electrode near12 indium adj oxide and (plug contact) near12 (tungsten w) near12 (dielectric insulation insulator) near12 (tantalum adj oxide "ta.sub.2 o.sub.5")	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/14 16:50
	0	indium adj oxide and (plug contact) near12 (tungsten w) near12 (dielectric insulation insulator) near12 (tantalum adj oxide "ta.sub.2 o.sub.5")	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/14 16:51
	6	capacitor near12 indium adj oxide	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/14 16:52
	0	capacitor near12 indium adj oxide and tantalum adj oxide	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/14 16:52

	0	capacitor near12 indium adj oxide and ("ta. <sub>sub.2</sub> o. <sub>sub.5</sub> " tantalum adj oxide)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/06/14 16:53
	2	capacitor near12 ("in. <sub>sub.2</sub> o. <sub>sub.3</sub> " indium adj oxide) and ("ta. <sub>sub.2</sub> o. <sub>sub.5</sub> " tantalum adj oxide)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/06/14 16:54
	0	capacitor near12 ("in. <sub>sub.2</sub> o. <sub>sub.3</sub> " indium adj oxide) and ("ta. <sub>sub.2</sub> o. <sub>sub.5</sub> " tantalum adj oxide) and (plug contact) near12 (tungsten w)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/06/14 16:55
	1	capacitor near12 ("in. <sub>sub.2</sub> o. <sub>sub.3</sub> " indium adj oxide) and ("ta. <sub>sub.2</sub> o. <sub>sub.5</sub> " tantalum adj oxide) and (plug contact)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/06/14 16:59
	1	capacit\$4 near12 ("in. <sub>sub.2</sub> o. <sub>sub.3</sub> " indium adj oxide) and ("ta. <sub>sub.2</sub> o. <sub>sub.5</sub> " tantalum adj oxide) and (plug contact)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/06/14 16:59
	210	(electrode capacit\$4) near12 ("in. <sub>sub.2</sub> o. <sub>sub.3</sub> " indium adj oxide) and ("ta. <sub>sub.2</sub> o. <sub>sub.5</sub> " tantalum adj oxide) and (plug contact)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/06/14 17:00
	3	(electrode capacit\$4) near12 ("in. <sub>sub.2</sub> o. <sub>sub.3</sub> " indium adj oxide) and ("ta. <sub>sub.2</sub> o. <sub>sub.5</sub> " tantalum adj oxide) and (plug contact) near12 (tungsten w)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/06/14 17:48
	3	283441.AP.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/06/14 17:20
	19	dram and stacked adj capacitor and (tantalum adj oxide tantalum adj pentoxide) and (indium adj oxide or ito)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/06/14 18:04
	58	(dram stacked adj capacitor) and (tantalum adj oxide tantalum adj pentoxide) and (indium adj oxide or ito)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/06/14 20:08
	39	((dram stacked adj capacitor) and (tantalum adj oxide tantalum adj pentoxide) and (indium adj oxide or ito)) not (dram and stacked adj capacitor and (tantalum adj oxide tantalum adj pentoxide) and (indium adj oxide or ito))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/06/14 18:05
	39	((dram stacked adj capacitor) and (tantalum adj oxide tantalum adj pentoxide) and (indium adj oxide or ito)) not (dram and stacked adj capacitor and (tantalum adj oxide tantalum adj pentoxide) and (indium adj oxide or ito))) and (dram stacked adj capacitor) and (tantalum adj oxide tantalum adj pentoxide) and (indium adj oxide or ito)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/06/14 19:03
	2	("6168991").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/06/14 19:09

	2	("613C123").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/14 19:09
	2	barrier near12 ("tan.sub.x" or tantalum adj nitride) and (tantalum adj oxide tantalum adj pentoxide) and (indium adj oxide or ito) near12 electrode	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/14 20:12
	1	barrier near12 ("tan.sub.x" or tantalum adj nitride) and (tantalum adj oxide tantalum adj pentoxide) and (indium adj oxide or ito) near12 electrode and tungsten	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/14 20:13
	2	("5696017").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/14 20:13
	0	("(contact or plug) near6 titanium adj nitride near12 tungsten").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/14 20:41
	339	(contact or plug) near6 titanium adj nitride near12 tungsten	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/14 21:38
	2	(contact or plug) near6 titanium adj nitride near12 tungsten and indium adj oxide	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/14 21:39
	3132	indium adj oxide near (crystal adj growth near12 non-parallel near12 channel) upper adj electrode and dram	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/14 21:40
	0	indium adj oxide near6 upper adj electrode and dram	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/14 21:41
	0	("in.sub.2 o.sub.3" indium adj oxide) near6 upper adj electrode and dram	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/14 21:41
	0	("in.sub.2 o.sub.3" indium adj oxide) near6 (cell upper) adj electrode and dram	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/14 21:55
	0	barnak.in. and mosfet adj get.ti.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/14 21:55
	1	barnak.in. and mosfet adj gate.ti.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/14 21:56
	2	("6168991").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/15 10:38

	1	(("6168991").PN.) and (tantalum adj nitride or "tan.sub.x")	USPAT; US_PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/15 10:40
	1	(("6168991").PN.) and (tantalum adj nitride or "tan.sub.x") and tungsten	USPAT; US_PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/15 10:41
	0	tantalum adj nitride near12 barrier near12 work adj function	USPAT; US_PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/15 10:42
	0	tantalum adj nitride near12 barrier near12 bcc	USPAT; US_PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/15 10:42
	12	tantalum adj nitride near12 barrier and bcc	USPAT; US_PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/15 10:43
	35	(US-6297527-\$ or US-6346454-\$ or US-5274482-\$ or US-5965942-\$ or US-5828129-\$ or US-5691220-\$ or US-6004839-\$ or US-6204076-\$ or US-6320244-\$ or US-5696017-\$ or US-5113273-\$ or US-5612574-\$ or US-6008123-\$ or US-6271596-\$ or US-6130123-\$ or US-5489548-\$ or US-5554564-\$ or US-5644151-\$ or US-5554866-\$ or US-5811851-\$ or US-6028360-\$ or US-6168991-\$ or US-6255151-\$ or US-6265260-\$ or US-4663559-\$).did. or (US-20010052608-\$ or US-20020008257-\$ or US-20020162738-\$ or US-20020096724-\$ or US-20020020875-\$).did. or (JP-09246494-\$ or JP-10320569-\$).did. or (US-20020008257-\$ or US-6130123-\$ or EP-539197-\$).did.	USPAT; US_PGPUB; JPO; DERWENT	2003/06/15 10:54
	4	((US-6297527-\$ or US-6346454-\$ or US-5274482-\$ or US-5965942-\$ or US-5828129-\$ or US-5691220-\$ or US-6004839-\$ or US-6204076-\$ or US-6320244-\$ or US-5696017-\$ or US-5113273-\$ or US-5612574-\$ or US-6008123-\$ or US-6271596-\$ or US-6130123-\$ or US-5489548-\$ or US-5554564-\$ or US-5644151-\$ or US-5554866-\$ or US-5811851-\$ or US-6028360-\$ or US-6168991-\$ or US-6255151-\$ or US-6265260-\$ or US-4663559-\$).did. or (US-20010052608-\$ or US-20020008257-\$ or US-20020162738-\$ or US-20020096724-\$ or US-20020020875-\$).did. or (JP-09246494-\$ or JP-10320569-\$).did. or (US-20020008257-\$ or US-6130123-\$ or EP-539197-\$).did.) and nishioka.in.	USPAT; US_PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/15 10:55

	4	( (US-6297527-\$ or US-6346454-\$ or US-5274482-\$ or US-5965942-\$ or US-5828129-\$ or US-5691220-\$ or US-6004839-\$ or US-6204076-\$ or US-6320244-\$ or US-5696017-\$ or US-5113273-\$ or US-5612574-\$ or US-6008123-\$ or US-6271596-\$ or US-6130123-\$ or US-5489548-\$ or US-5554564-\$ or US-5644151-\$ or US-5554866-\$ or US-5811851-\$ or US-6028360-\$ or US-6168991-\$ or US-6255151-\$ or US-6265260-\$ or US-4663559-\$).did. or (US-20010052608-\$ or US-20020008257-\$ or US-20020162738-\$ or US-20020096724-\$ or US-20020020875-\$).did. or (JP-09246494-\$ or JP-10320569-\$).did. or (US-20020008257-\$ or US-6130123-\$ or EP-539197-\$).did.) and nishioka.in. and (indium adj oxide or "insub.2 o.sub.3") diffusion adj barrier with tantal\$2 adj nitride	USPAT; US-PPGPUB; EPO; JPO; DERWENT; IBM TDB	2003/06/15 10:56
	465		USPAT; US-PPGPUB; EPO; JPO; DERWENT; IBM TDB	2003/08/20 11:04
	35	(US-5691220-\$ or US-6320244-\$ or US-5696017-\$ or US-5113273-\$ or US-5612574-\$ or US-6008123-\$ or US-6297527-\$ or US-6130123-\$ or US-6168991-\$ or US-6028360-\$ or US-5811851-\$ or US-5554866-\$ or US-5644151-\$ or US-5554564-\$ or US-5489548-\$ or US-6204076-\$ or US-5965942-\$ or US-6255151-\$ or US-4663559-\$ or US-5274482-\$ or US-6346454-\$ or US-6004839-\$ or US-5828129-\$ or US-6265260-\$ or US-6271596-\$).did. or (US-20020162738-\$ or US-20020096724-\$ or US-20020020875-\$ or US-20020008257-\$ or US-20010052608-\$).did. or (JP-09246494-\$ or JP-10320569-\$).did. or (US-6130123-\$ or EP-539197-\$ or US-20020008257-\$).did.	USPAT; US-PPGPUB; JPO; DERWENT	2003/12/22 15:51
	4	499037.ap.	USPAT; US-PPGPUB; EPO; JPO; DERWENT; IBM TDB	2003/12/23 14:29